

MOSFET - Power, DUAL COOL[®] N-Channel, PQFN8 150 V, 11.4 mΩ, 80 A NTMFSC012N15MC

Features

- Advanced Dual-sided Cooled Packaging
- Ultra Low $R_{DS(on)}$
- MSL1 Robust Packaging Design

Typical Applications

- Primary DC-DC FET
- Synchronous Rectifier
- DC-DC Conversion

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	150	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain Current R _{θJC} (Notes 1, 3)	Steady State	T _C = 25°C	I _D	80	A
		T _C = 100°C		50	
Power Dissipation R _{θJC} (Note 1)		T _C = 25°C	P _D	147	W
		T _C = 100°C		58	
Continuous Drain Current R _{θJA} (Notes 1, 2, 3)	Steady State	T _A = 25°C	I _D	10	A
		T _A = 100°C		6	
Power Dissipation R _{θJA} (Notes 1, 2)		T _A = 25°C	P _D	2.7	W
		T _A = 100°C		1	
Pulsed Drain Current	T _C = 25°C, t _p = 10 μs		I _{DM}	1067	A
Operating Junction / Storage Temperature Max			T _J , T _{stg}	+150	°C
Source Current (Body Diode)			I _S	122	A
Single Pulse Drain-to-Source Avalanche Energy (I _{L(pk)} = 35 A)			E _{AS}	161	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

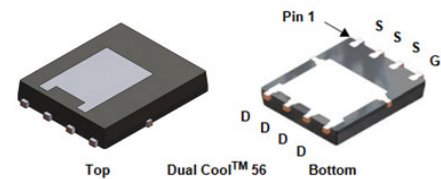
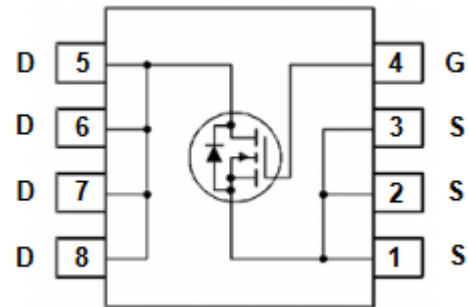
THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State	$R_{\theta JC}$	0.85	$^\circ\text{C/W}$
Junction-to-Case Top - Steady State	$R_{\theta JT}$	1.5	
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	46	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

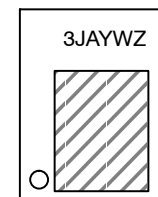
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
150 V	11.4 mΩ @ 10 V	44 A
	14.5 mΩ @ 8 V	22 A

N-CHANNEL MOSFET



DFN8 5x6.15
CASE 506EG

MARKING DIAGRAM



- 3J = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- Z = Assembly Lot Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NTMFSC012N15MC	PQFN8 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTMFSC012N15MC

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\text{ }\mu\text{A}$, ref to 25°C		6.9		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 150\text{ V}$	$T_J = 25^\circ\text{C}$		1	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 194\text{ }\mu\text{A}$	2.5		4.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 194\text{ }\mu\text{A}$, ref to 25°C		8		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 44\text{ A}$		8.9	11.4	m Ω
		$V_{GS} = 8\text{ V}, I_D = 22\text{ A}$		9.5	14.5	
Gate-Resistance	R_G	$T_A = 25^\circ\text{C}$		0.7		Ω

CHARGES & CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 75\text{ V}$		2490		pF
Output Capacitance	C_{OSS}			676		
Reverse Transfer Capacitance	C_{RSS}			9.0		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 6\text{ V}, V_{DS} = 75\text{ V}, I_D = 44\text{ A}$		20.4		nC
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 75\text{ V}, I_D = 44\text{ A}$		32.4		
Gate-to-Source Charge	Q_{GS}			13.9		
Gate-to-Drain Charge	Q_{GD}			5.5		
Plateau Voltage	V_{GP}			5.7		V

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 75\text{ V}, I_D = 44\text{ A}, R_G = 2.5\text{ }\Omega$		18.4		ns
Rise Time	t_r			3.7		
Turn-Off Delay Time	$t_{d(OFF)}$			21.3		
Fall Time	t_f			3		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 44\text{ A}$	$T_J = 25^\circ\text{C}$		0.88	V
			$T_J = 125^\circ\text{C}$		0.76	
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 1000\text{ A}/\mu\text{s}, I_S = 44\text{ A}$		42.7		ns
Reverse Recovery Charge	Q_{RR}			559		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

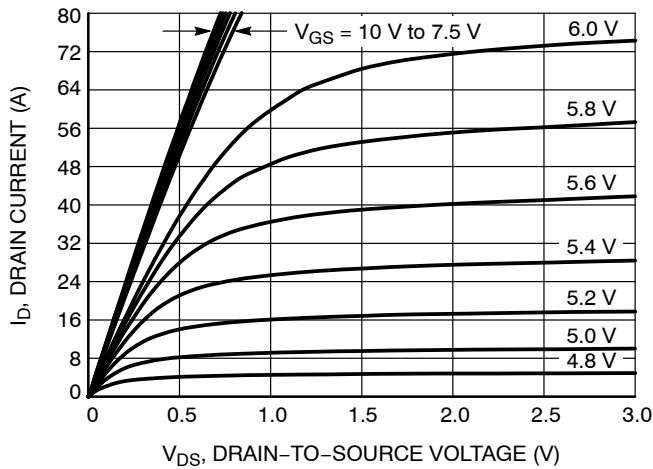


Figure 1. On-Region Characteristics

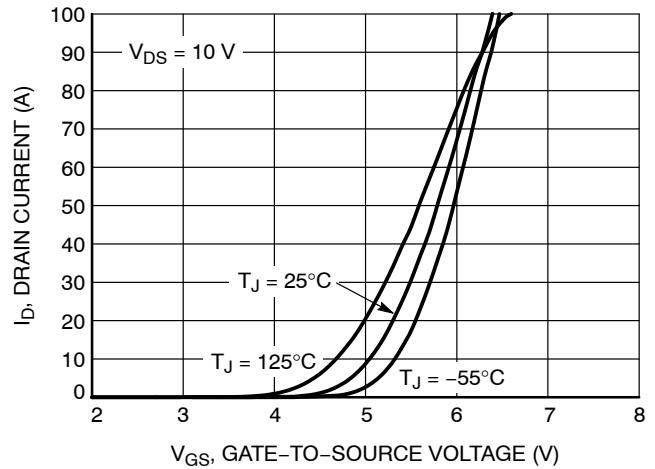


Figure 2. Transfer Characteristics

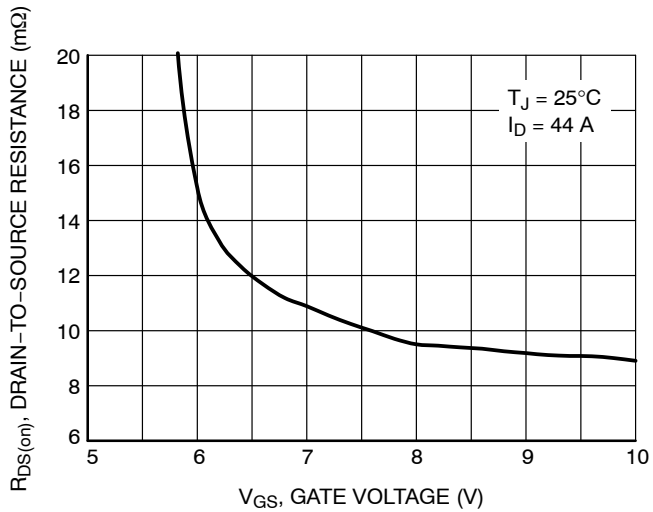


Figure 3. On-Resistance vs. Gate-to-Source Voltage

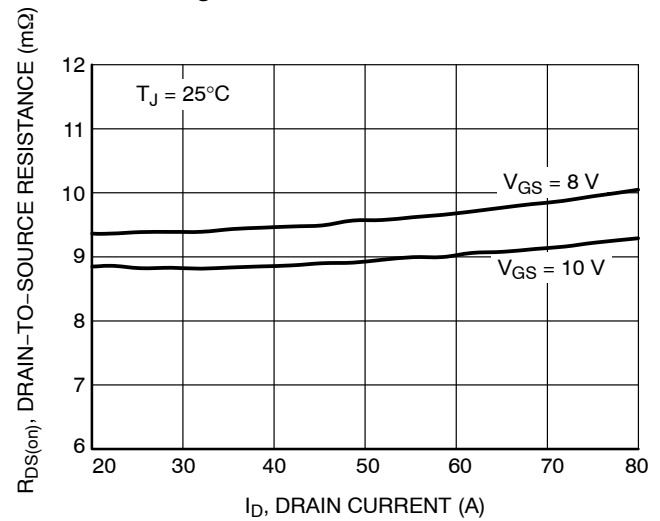


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

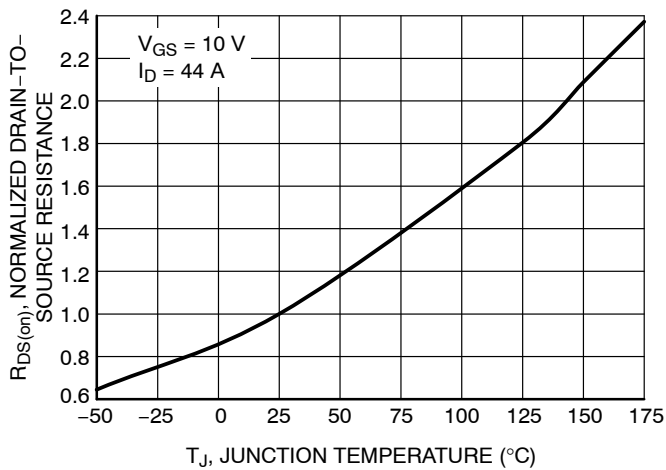


Figure 5. On-Resistance Variation with Temperature

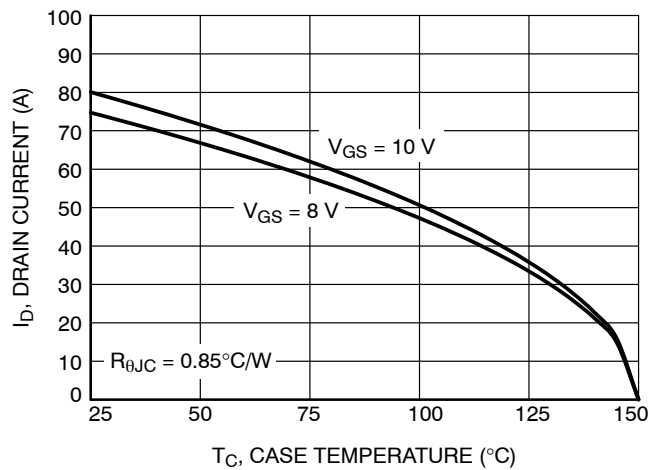


Figure 6. Maximum Continuous Drain Current vs. Case Temperature

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TYPICAL CHARACTERISTICS

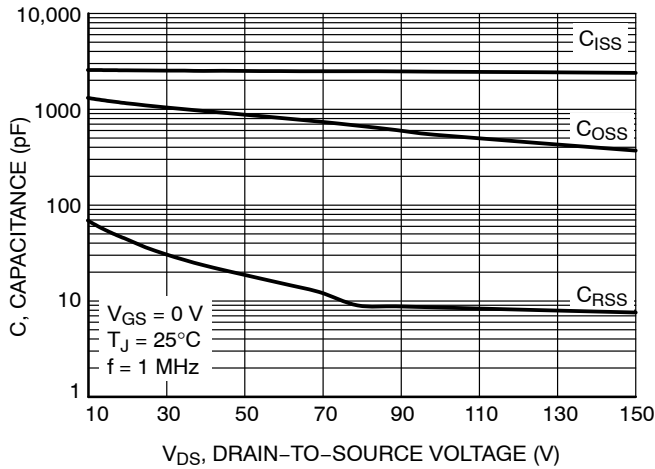


Figure 7. Capacitance Variation

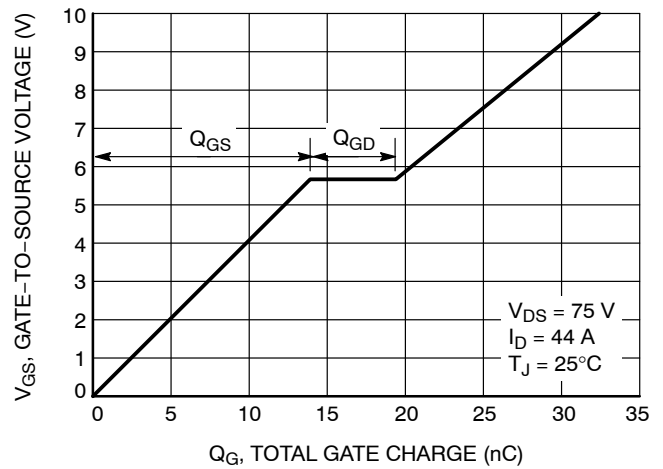


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

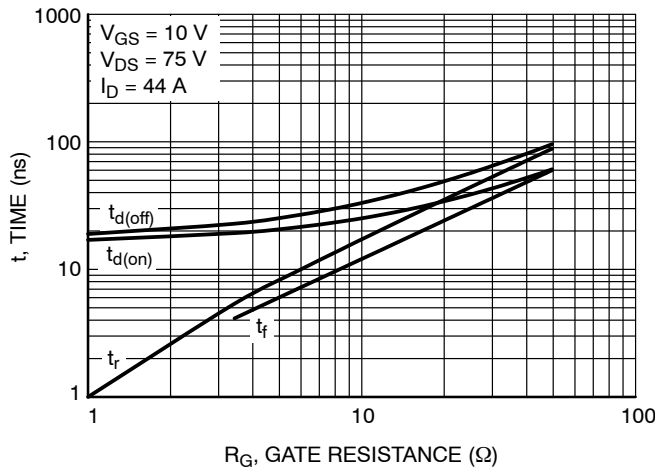


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

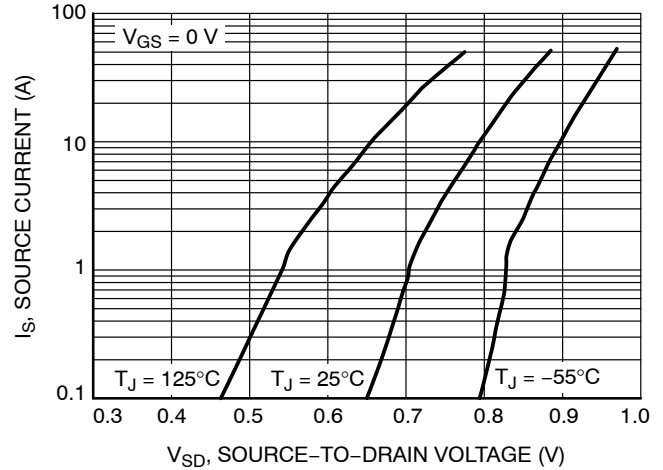


Figure 10. Diode Forward Voltage vs. Current

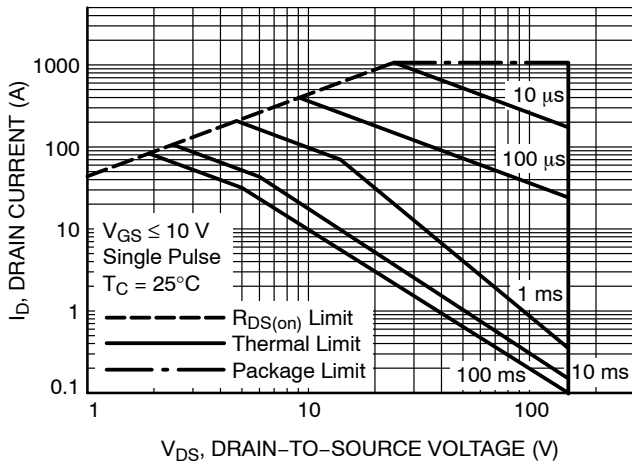


Figure 11. Safe Operating Area

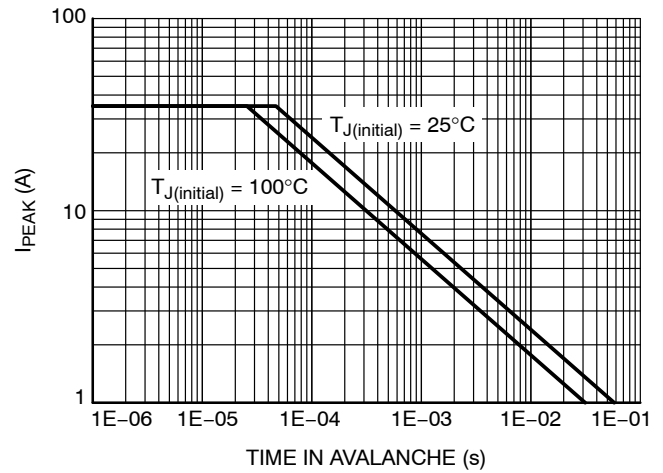


Figure 12. I_{PEAK} vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

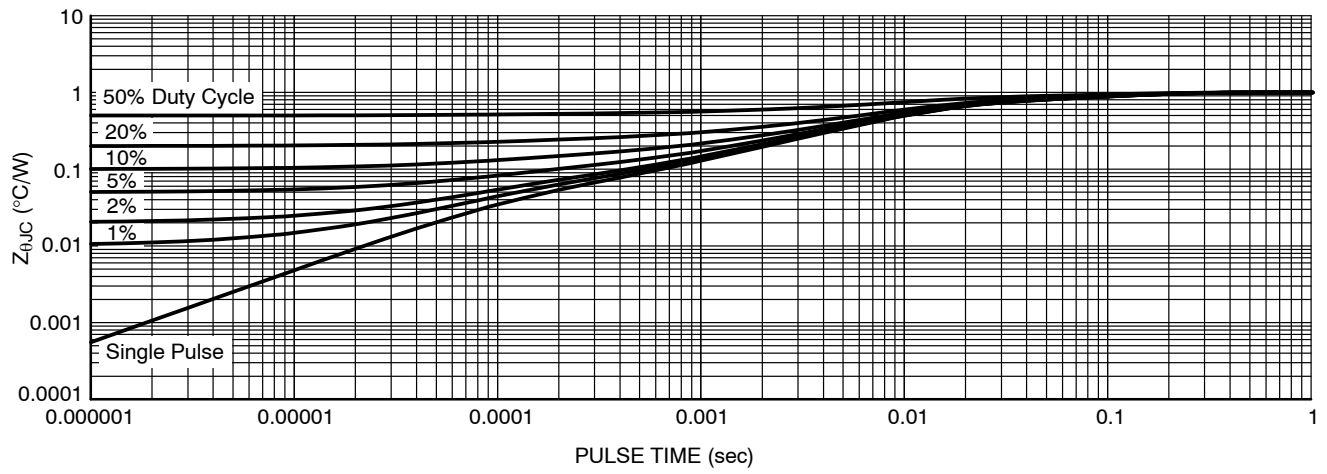
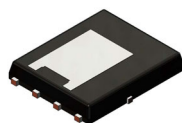
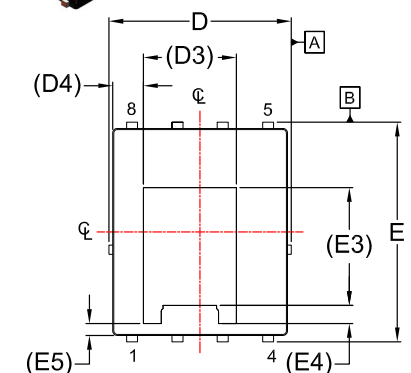


Figure 13. Thermal Characteristics

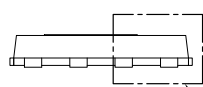
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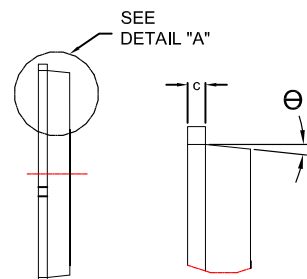


TOP VIEW



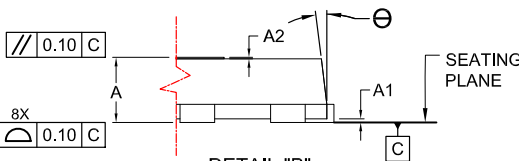
FRONT VIEW

SEE
DETAIL "B"



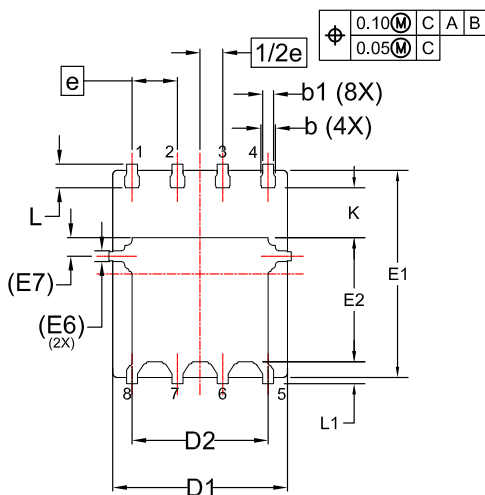
SIDE VIEW

DETAIL "A"
SCALE: 2:1



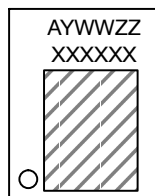
DETAIL "B"

SCALE: 2-1



BOTTOM VIEW

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.


- NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.85	0.90	0.95
A1	-	-	0.05
A2	-	-	0.05
b	0.31	0.41	0.51
b1	0.21	0.31	0.41
c	0.20	0.25	0.30
D	4.90	5.00	5.10
D1	4.80	4.90	5.00
D2	3.67	3.82	3.97
D3	2.60 REF		
D4	0.86 REF		
E	6.05	6.15	6.25
E1	5.70	5.80	5.90
E2	3.38	3.48	3.58
E3	3.30 REF		
E4	0.50 REF		
E5	0.34 REF		
E6	0.30 REF		
E7	0.52 REF		
e	1.27 BSC		
1/2e	0.635 BSC		
K	1.30	1.40	1.50
L	0.56	0.66	0.76
L1	0.52	0.62	0.72
Ø	0°	---	12°

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